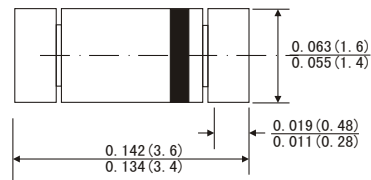


FEATURES

- Metal-on-silicon junction
- High breakdown voltage
- Low turn-on voltage
- Ultrafast switching speed
- Primarily intended for high level UHF/VHF detection and pulse applications with broad dynamic range.
- The diode is also available in the DO-35 case with type designation 1N5712.
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



MiniMELF



Dimensions in inches and (millimeters)

MECHANICAL DATA

- Case: MiniMELF glass case(SOD-80)
- Weight: Approx. 0.05 gram

ABSOLUTE RATINGS(LIMITING VALUES)

| | Symbols | Value | Units |
|---|----------------------------------|------------|-------|
| Peak Reverse Voltage | V _{RRM} | 20 | V |
| Power Dissipation (infinite Heat Sink) | P _{tot} | 430 | mW |
| Forward Continuous Current | I _F | 35 | mA |
| Operation and storage temperature range | T _A /T _{STG} | -55 to+150 | °C |

ELECTRICAL CHARACTERISTICS

| | Symbols | Min. | Typ. | Max. | Units |
|--|------------------|------|------|------|-------|
| Reverse breakover voltage at I _R =10μA | V _R | 20 | | | V |
| Leakage current at V _R =15V | I _R | | | 100 | nA |
| Forward voltage drop at I _F =1mA | V _F | | | 0.41 | V |
| Test pulse: t _p ≤ 300μs δ < 2% I _F =35mA | V _F | | | 1.0 | V |
| Junction Capacitance at V _R =0V, f=1MHz | C _J | | | 1.2 | pF |
| Thermal resistance | R _{θJA} | | | 400 | K/W |

RATINGS AND CHARACTERISTICS CURVES LL5712

Figure 1. forward current versus forward voltage at different temperatures(typical values)

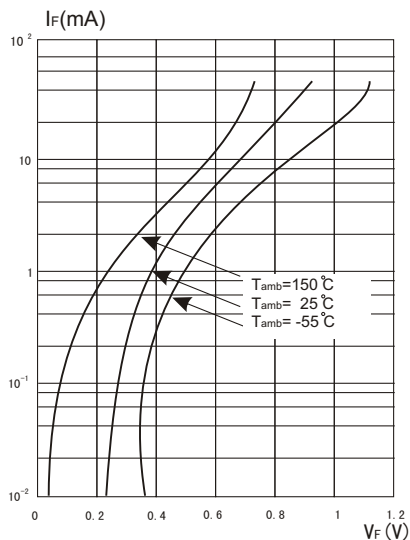


Figure 2. forward current versus forward voltage (typical values)

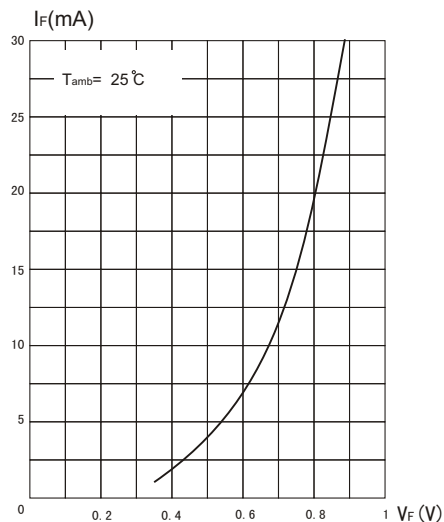
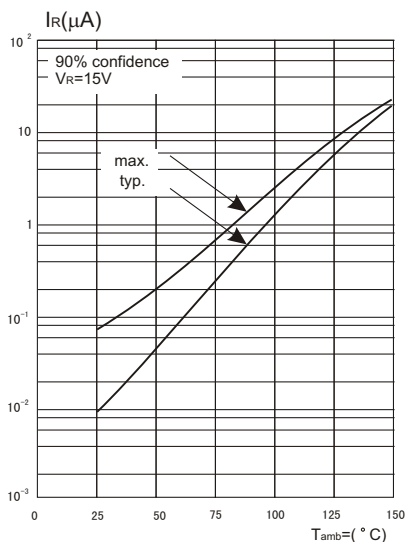


Figure 3. Reverse current versus ambient temperature



RATINGS AND CHARACTERISTICS CURVES LL5712

Figure 4.Reverse current versus continuous Reverse voltage(typical values)

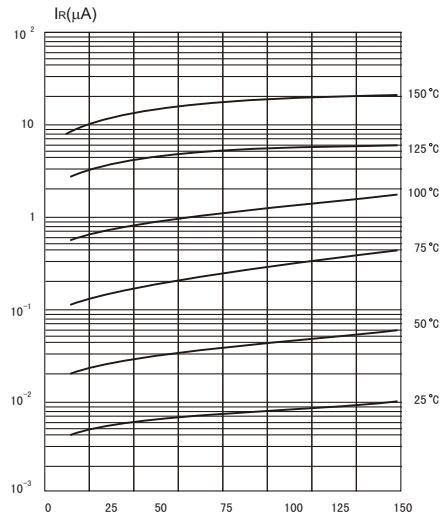


Figure 5.Capacitance C_J versus revers applied voltage V_R (typical values)

